



Sheet 1 of 6

Form 1449*	Atty. Docket No.: 303.672US1	Serial No. 09/483,881
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Kie Y. Ahn et al.	
	Filing Date: January 18, 2000	Group: Unknown

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date Appropriate
hm	2,842,438	07/08/1958	Saarivirta, M.J., et al.	75	153	08/02/56
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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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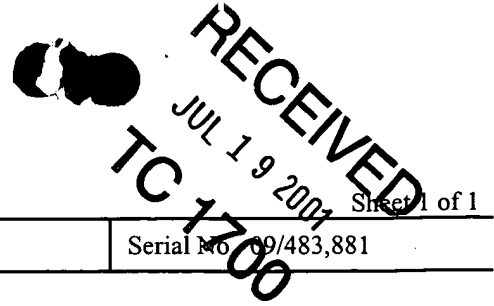
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		5,084,412 /	01/28/1992	Nakasaki, Y.	437	189	10/01/90
		5,231,056 /	07/27/1993	Sandhu, G.S.	437	200	01/15/92
		5,654,245 /	08/05/1997	Allen, G.L.	438	629	03/23/93
		5,670,420 /	09/23/1997	Choi, K.K.	437	189	11/08/95
		5,763,953 /	06/09/1998	Iljima, T., et al.	257	762	01/18/96
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		6,140,228 /	10/31/2000	Shan, ., et al.	438	653	11/13/97
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		6,153,507 /	11/28/2000	Mikagi, K.	438	618	01/13/98
		6,171,661 /	01/09/2001	Zheng, B., et al.	427	535	02/25/98
		6,197,688 /	03/06/2001	Simpson, C.R.	438	678	02/12/98
		6,207,222 /	03/27/2001	Chen, L., et al.	427	97	08/24/99

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Initial							Yes	No
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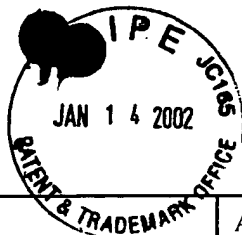
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		6,015,465	01/18/2000	Kholodenko, A., et al.	118	719	04/08/98
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